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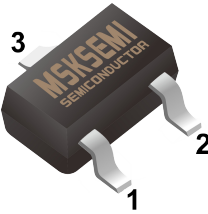
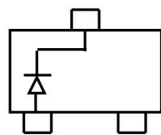
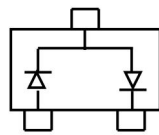
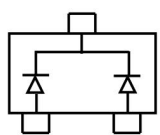
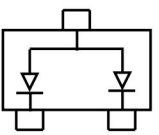
BAS70W/-04/-05/-06

Product specification

FEATURES

- Low turn-on voltage
- Fast switching
- Also available in lead free version

Reference News

PACKAGE OUTLINE	BAS70W	BAS70W-04	BAS70W-05	BAS70W-06
				
	K73	K74	K75	K76
SOT-323	MARKING:K73	MARKING:K74	MARKING:K75	MARKING:K76

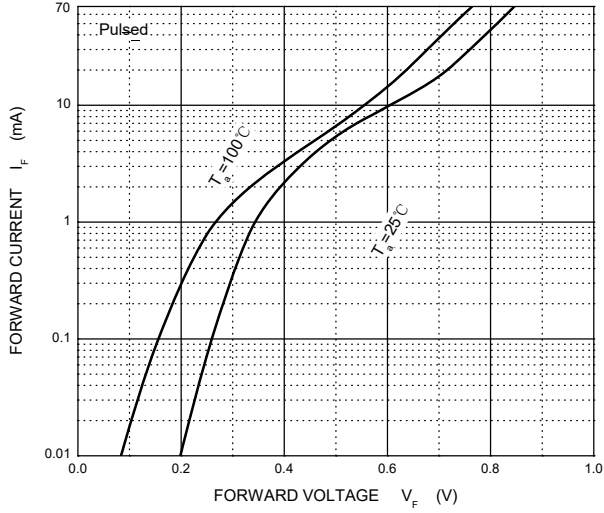
Maximum Ratings @Ta=25°C

Symbol	Parameter	Value	Unit
V_R	DC Voltage	70	V
I_F	Forward Continuous Current	70	mA
I_{FSM}	Non-Repetitive Peak Forward Surge Current @ t = 8.3ms	100	mA
P_D	Power Dissipation	200	mW
$R_{\theta JA}$	Thermal Resistance from Junction to Ambient	500	°C/W
T_J	Operating Junction Temperature Range	-40 ~ +125	°C
T_{stg}	Storage Temperature Range	-55 ~ +150	°C

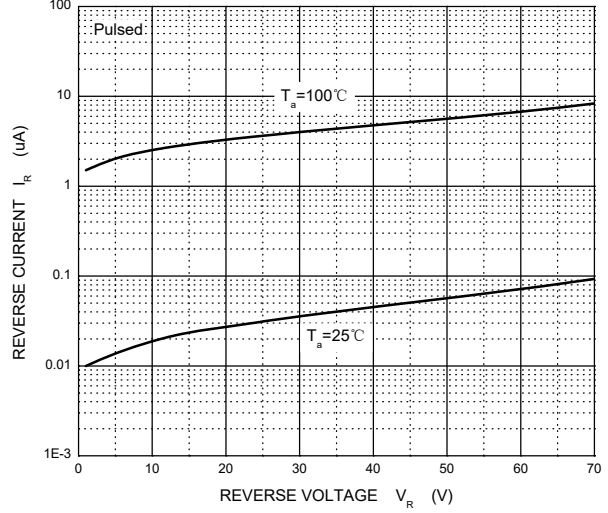
ELECTRICAL CHARACTERISTICS (Ta=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Max	Unit
Reverse breakdown voltage	$V_{(BR)}$	$I_R=10\mu A$	70		V
Reverse voltage leakage current	I_R	$V_R=50V$		100	nA
Forward voltage	V_F	$I_F=1mA$ $I_F=15mA$		410 1000	mV
Diode capacitance	C_D	$V_R=0V, f=1MHz$		2	pF
Revers recovery time	t_{rr}	$I_F=I_R=10mA, I_{rr}=0.1 \times I_R,$ $R_L=100\Omega$		5	ns

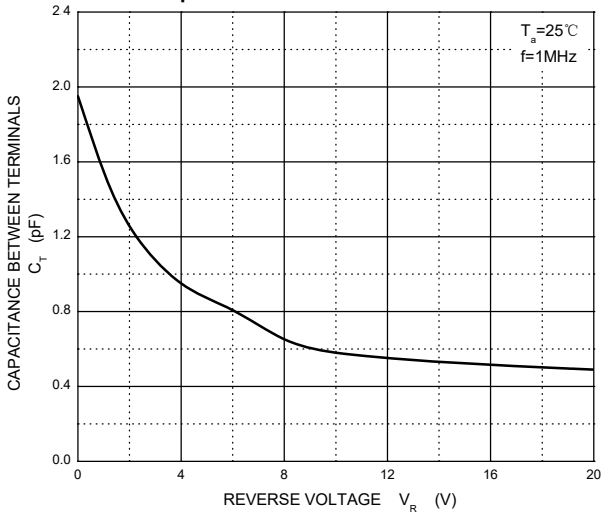
Forward Characteristics



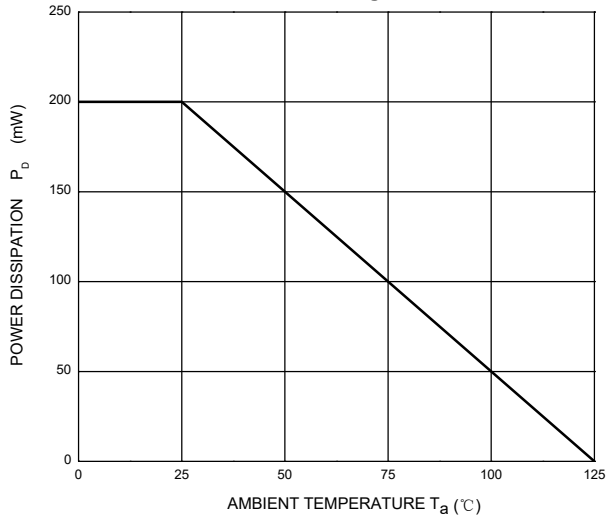
Reverse Characteristics



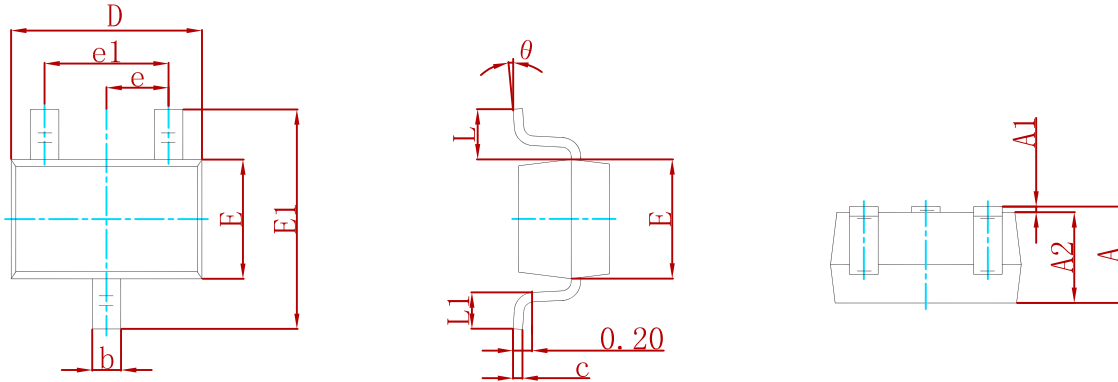
Capacitance Characteristics Per Diode



Power Derating Curve

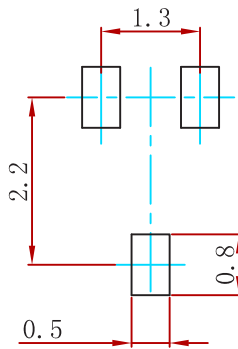


PACKAGE MECHANICAL DATA



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	0.900	1.100	0.035	0.043
A1	0.000	0.100	0.000	0.004
A2	0.900	1.000	0.035	0.039
b	0.200	0.400	0.008	0.016
c	0.080	0.150	0.003	0.006
D	2.000	2.200	0.079	0.087
E	1.150	1.350	0.045	0.053
E1	2.150	2.450	0.085	0.096
e	0.650 TYP		0.026 TYP	
e1	1.200	1.400	0.047	0.055
L	0.525 REF		0.021 REF	
L1	0.260	0.460	0.010	0.018
θ	0°	8°	0°	8°

Suggested Pad Layout



- Note:
1. Controlling dimension: in millimeters.
 2. General tolerance: ± 0.05 mm.
 3. The pad layout is for reference purposes only.

REEL SPECIFICATION

P/N	PKG	QTY
BAS70W/-04/-05/-06	SOT-323	3000

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